

IRF9520NSPbF

IRF9520NLPbF

HEXFET® Power MOSFET

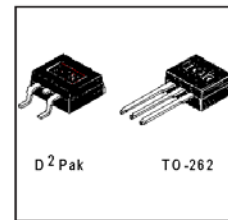
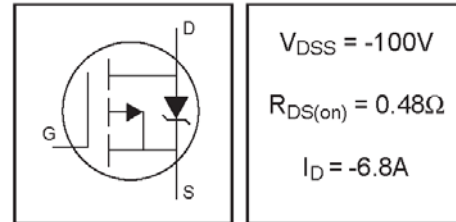
- Advanced Process Technology
- Surface Mount (IRF9520S)
- Low-profile through-hole (IRF9520L)
- 175°C Operating Temperature
- Fast Switching
- P-Channel
- Fully Avalanche Rated
- Lead-Free

Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The D²Pak is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D²Pak is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0W in a typical surface mount application.

The through-hole version (IRF9520L) is available for low-profile applications.



Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V$ ⑤	-6.8	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ -10V$ ⑤	-4.8	
I_{DM}	Pulsed Drain Current ①⑤	-27	
$P_D @ T_A = 25^\circ C$	Power Dissipation	3.8	W
$P_D @ T_C = 25^\circ C$	Power Dissipation	48	W
	Linear Derating Factor	0.32	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy②⑤	140	mJ
I_{AR}	Avalanche Current①	-4.0	A
E_{AR}	Repetitive Avalanche Energy①	4.8	mJ
dv/dt	Peak Diode Recovery dv/dt ③⑤	-5.0	V/ns
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds		

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	---	3.1	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB Mounted, steady-state)**	---	40	

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Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-100	---	---	V	$V_{GS} = 0V, I_D = -250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	---	-0.10	---	V/°C	Reference to $25^\circ\text{C}, I_D = -1\text{mA}$ ⑤
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	---	---	0.48	Ω	$V_{GS} = 10V, I_D = -4.0A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	-2.0	---	-4.0	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
g_{fs}	Forward Transconductance	1.4	---	---	S	$V_{DS} = -50V, I_D = -4.0A$ ⑤
I_{DSS}	Drain-to-Source Leakage Current	---	---	-25	μA	$V_{DS} = -100V, V_{GS} = 0V$
		---	---	-250		$V_{DS} = -80V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	---	---	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	---	---	-100		$V_{GS} = -20V$
Q_g	Total Gate Charge	---	---	27	nC	$I_D = -4.0A$
Q_{gs}	Gate-to-Source Charge	---	---	5.0		$V_{DS} = -80V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	---	---	15		$V_{GS} = -10V$, See Fig. 6 and 13 ④⑤
$t_{d(on)}$	Turn-On Delay Time	---	14	---	ns	$V_{DD} = -50V$
t_r	Rise Time	---	47	---		$I_D = -4.0A$
$t_{d(off)}$	Turn-Off Delay Time	---	28	---		$R_G = 22\Omega$
t_f	Fall Time	---	31	---		$R_D = 12\Omega$, See Fig. 10 ④⑤
L_S	Internal Source Inductance	---	7.5	---	nH	Between lead, and center of die contact
C_{iss}	Input Capacitance	---	350	---	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	---	110	---		$V_{DS} = -25V$
C_{rss}	Reverse Transfer Capacitance	---	70	---		$f = 1.0\text{MHz}$, See Fig. 5⑤

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	---	---	-6.8	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	---	---	-27		
V_{SD}	Diode Forward Voltage	---	---	-1.6	V	$T_J = 25^\circ\text{C}, I_S = -4.0A, V_{GS} = 0V$ ④
t_{rr}	Reverse Recovery Time	---	100	150	ns	$T_J = 25^\circ\text{C}, I_F = -4.0A$
Q_{rr}	Reverse Recovery Charge	---	420	630	nC	$di/dt = -100A/\mu s$ ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② Starting $T_J = 25^\circ\text{C}, L = 18\text{mH}$
 $R_G = 25\Omega, I_{AS} = -4.0A$. (See Figure 12)
- ③ $I_{SD} \leq -4.0A, di/dt \leq -300A/\mu s, V_{DD} \leq V_{(BR)DSS}, T_J \leq 175^\circ\text{C}$
- ④ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$
- ⑤ Uses IRF9520N data and test conditions

** When mounted on 1" square PCB (FR-4 or G-10 Material).
For recommended footprint and soldering techniques refer to application note #AN-994.

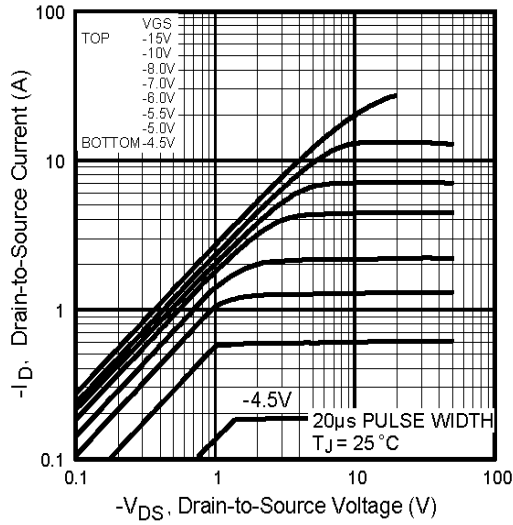


Fig 1. Typical Output Characteristics,

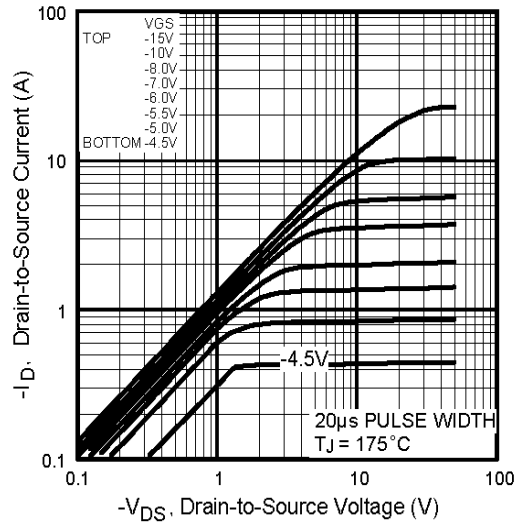


Fig 2. Typical Output Characteristics,

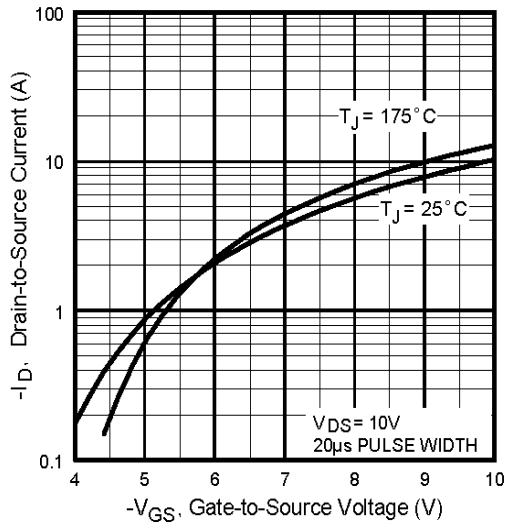


Fig 3. Typical Transfer Characteristics

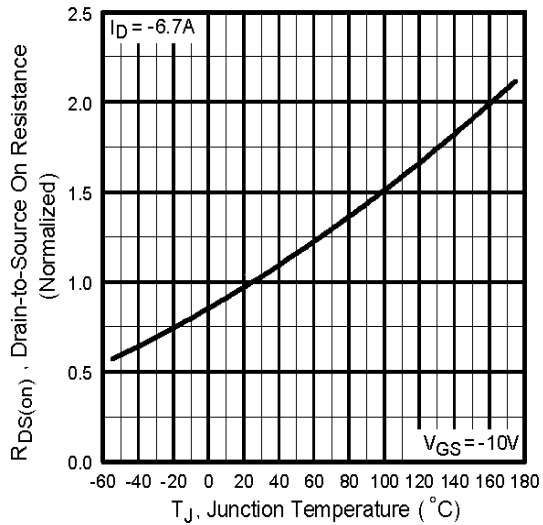


Fig 4. Normalized On-Resistance Vs. Temperature

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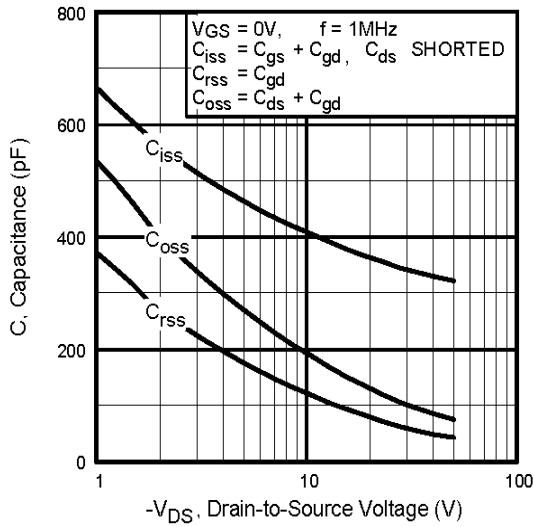


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

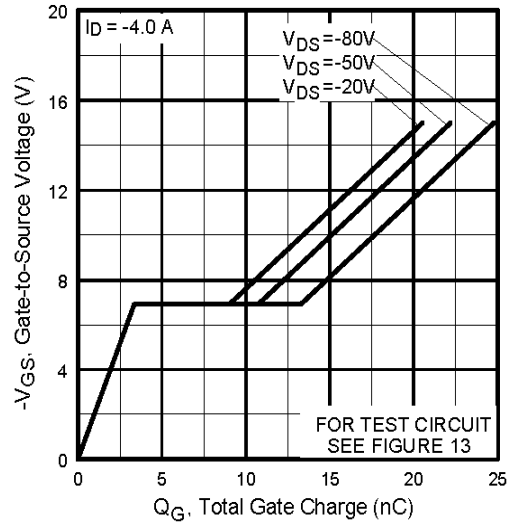


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

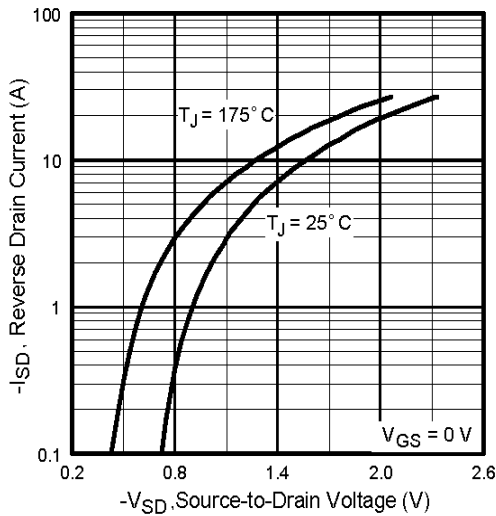


Fig 7. Typical Source-Drain Diode Forward Voltage

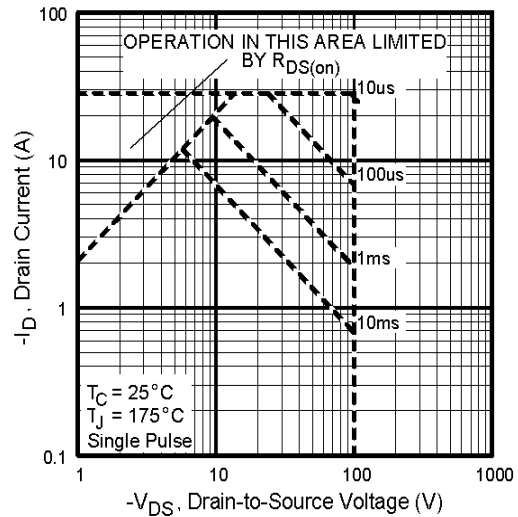


Fig 8. Maximum Safe Operating Area

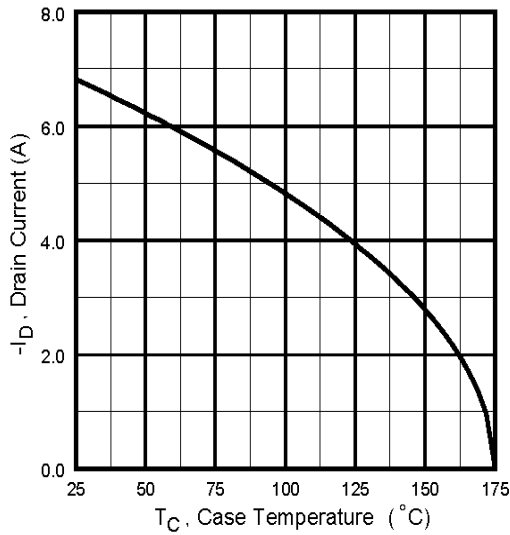


Fig 9. Maximum Drain Current Vs. Case Temperature

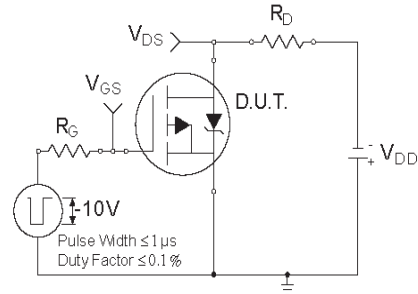


Fig 10a. Switching Time Test Circuit

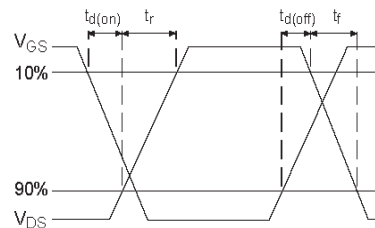


Fig 10b. Switching Time Waveforms

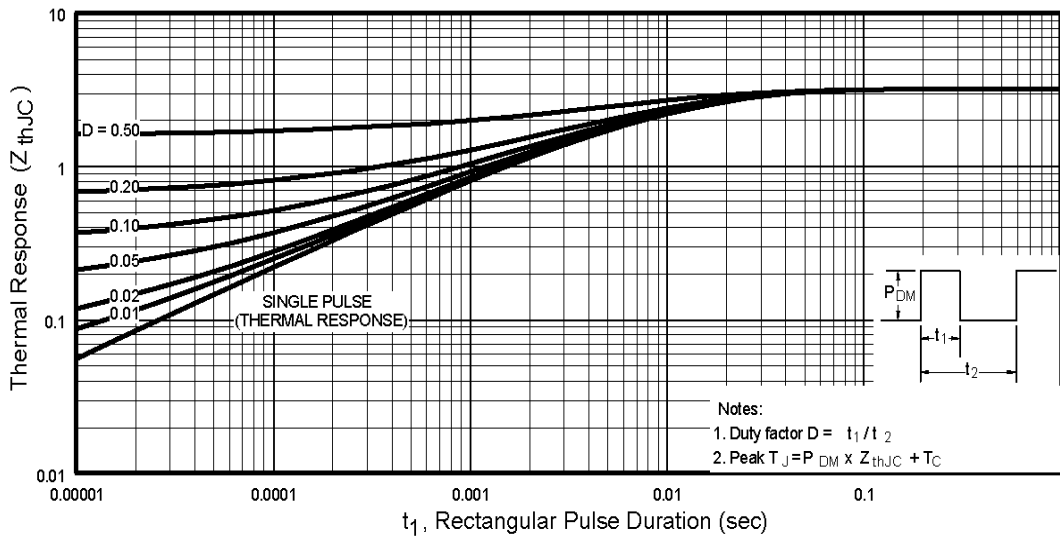


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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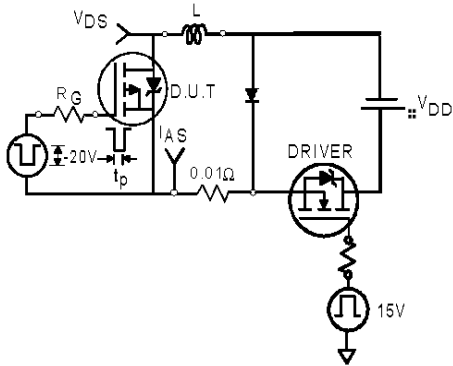


Fig 12a. Unclamped Inductive Test Circuit

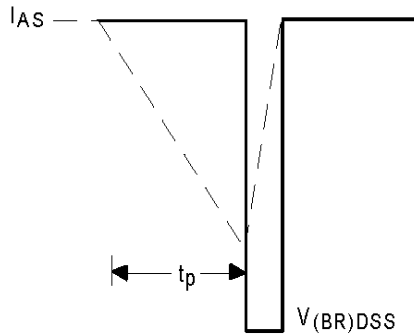


Fig 12b. Unclamped Inductive Waveforms

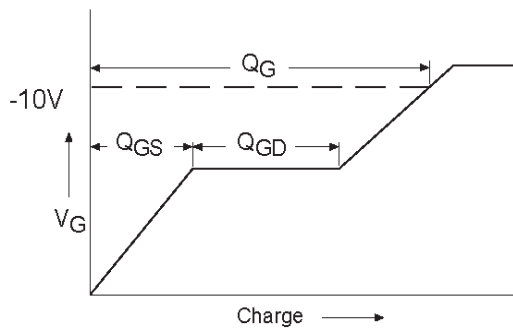


Fig 13a. Basic Gate Charge Waveform

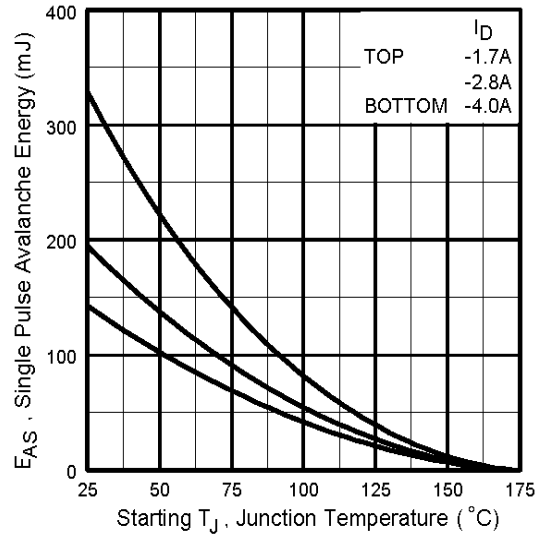


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

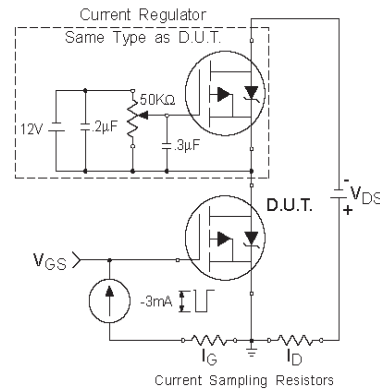
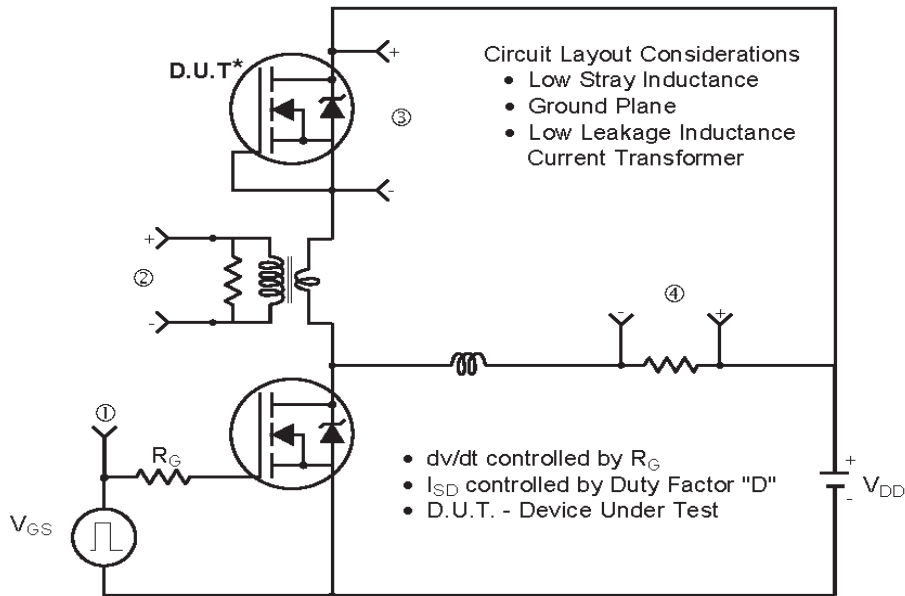
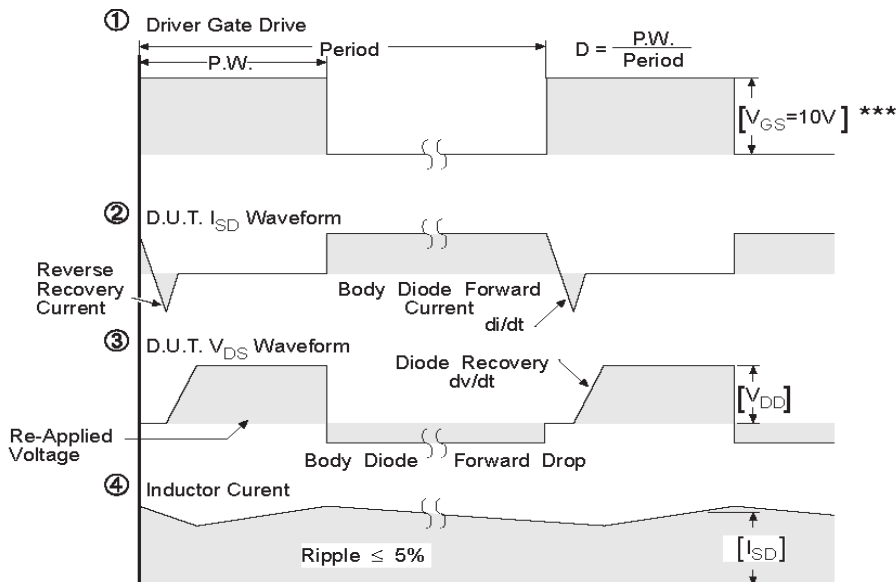


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



* Reverse Polarity of D.U.T. for P-Channel



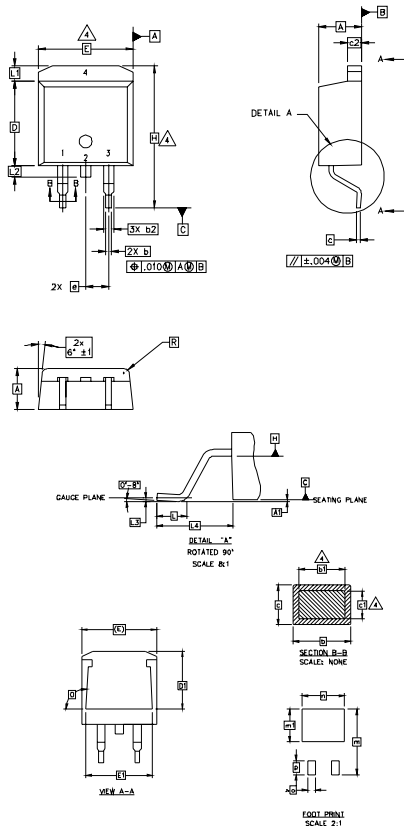
*** $V_{GS} = 5.0V$ for Logic Level and $3V$ Drive Devices

Fig 14. For P-Channel HEXFETS

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D²Pak Package Outline (Dimensions are shown in millimeters (inches))



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
5. CONTROLLING DIMENSION: INCH.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1	0.00	0.254	.000	.010	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	4
b2	1.14	1.78	.045	.070	
c	0.38	0.74	.015	.029	
c1	0.38	0.58	.015	.023	4
c2	1.14	1.65	.045	.065	
D	8.51	9.65	.335	.380	3
D1	6.86		.270		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
H	14.61	15.88	.575	.625	
L	1.78	2.79	.070	.110	
L1		1.65		.065	
L2	1.27	1.78	.050	.070	
L3	0.25 BSC		.010 BSC		
L4	4.78	5.28	.188	.208	
m	17.78		.700		
m1	8.89		.350		
n	11.43		.450		
o	2.08		.082		
p	3.81		.150		
R	0.51	0.71	.020	.028	
θ	90°	93°	90°	93°	

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2, 4.- DRAIN
- 3.- SOURCE

IGBTs, CoPACK

- 1.- GATE
- 2, 4.- COLLECTOR
- 3.- EMITTER

DIODES

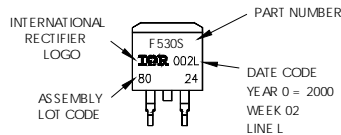
- 1.- ANODE *
- 2, 4.- CATHODE
- 3.- ANODE

* PART DEPENDENT.

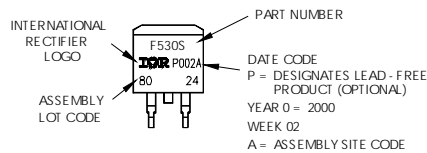
D²Pak Part Marking Information

EXAMPLE: THIS IS AN IRF530S WITH
LOT CODE 8024
ASSEMBLED ON WW02, 2000
IN THE ASSEMBLY LINE "L"

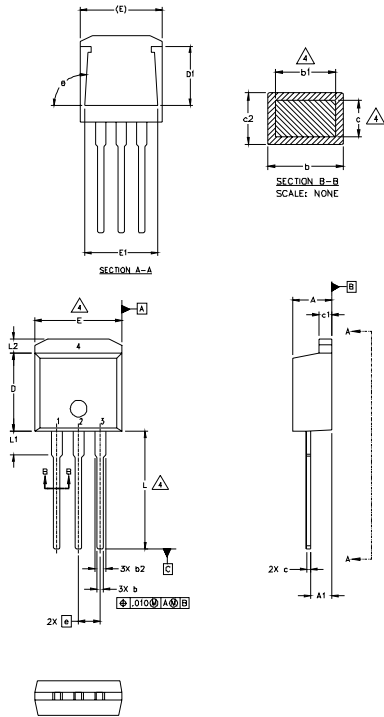
Note: "P" in assembly line position
indicates "Lead - Free"



OR



TO-262 Package Outline (Dimensions are shown in millimeters (inches))



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	4
A1	2.03	2.92	.080	.115	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	
b2	1.14	1.40	.045	.055	4
c	0.38	0.63	.015	.025	
c1	1.14	1.40	.045	.055	3
c2	0.43	.063	.017	.029	
D	8.51	9.65	.335	.380	3
D1	5.33		.210		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
L	13.46	14.09	.530	.555	
L1	3.56	3.71	.140	.146	
L2		1.65		.065	

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

IGBT

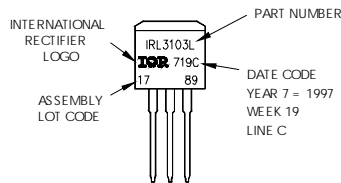
- 1 - GATE
- 2 - COLLECTOR
- 3 - EMITTER

NOTES:

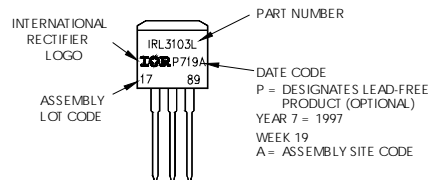
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
5. CONTROLLING DIMENSION: INCH.

TO-262 Part Marking Information

EXAMPLE: THIS IS AN IRL3103L
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"
Note: "P" in assembly line
position indicates "Lead-Free"



OR

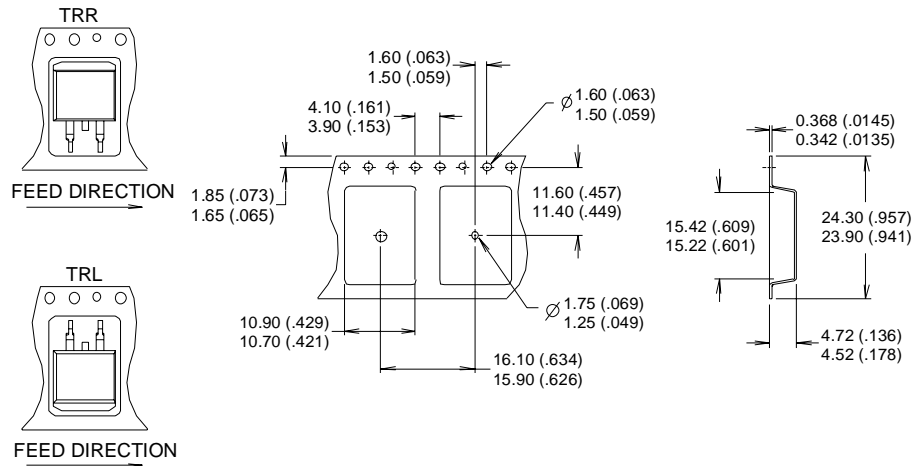


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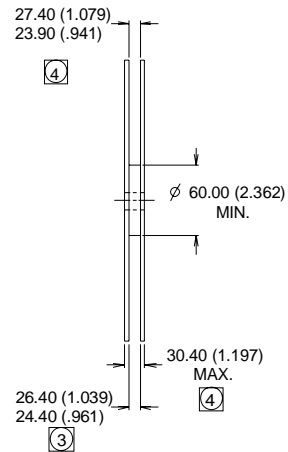
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D²Pak Tape & Reel Information

Dimensions are shown in millimeters (inches)



- NOTES:
1. CONFORMS TO EIA-418.
 2. CONTROLLING DIMENSION: MILLIMETER.
 - ③ DIMENSION MEASURED @ HUB.
 - ④ INCLUDES FLANGE DISTORTION @ OUTER EDGE.



Data and specifications subject to change without notice.

International
IR Rectifier

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TAC Fax: (310) 252-7903

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Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>

单击下面可查看定价，库存，交付和生命周期等信息

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